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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re application of: Hausmann et al.

Attorney Docket No.:  
NOVLP076/NVLS-002858

Application No.: NEW

Examiner: UNASSIGNED

Filed: HEREWITH

Group: UNASSIGNED

Title: IMPROVING THE PROPERTIES OF A  
SILICA THIN FILM PRODUCED BY A  
RAPID VAPOR DEPOSITION (RVD)  
PROCESS

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**INFORMATION DISCLOSURE STATEMENT  
37 CFR §§1.56 AND 1.97(b)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

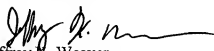
Dear Sir:

The references listed in the attached PTO Form 1449, copies of which are attached, may be material to examination of the above-identified patent application. Applicants submit these references in compliance with their duty of disclosure pursuant to 37 CFR §§1.56 and 1.97. The Examiner is requested to make these references of official record in this application.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that these references indeed constitute prior art.

This Information Disclosure Statement is: (i) filed within three (3) months of the filing date of the above-referenced application, (ii) believed to be filed before the mailing date of a first Office Action on the merits, or (iii) believed to be filed before the mailing of a first Office Action after the filing of a Request for Continued Examination under §1.114. Accordingly, it is believed that no fees are due in connection with the filing of this Information Disclosure Statement. However, if it is determined that any fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. NOVLP076).

Respectfully submitted,  
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<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	NOVLP076/NVLS-002858	Unassigned
	Applicant:	
	Hausmann et al.	
	Filing Date	Group
	HEREWITH	Unassigned

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1	6,511,539	1/28/03	Raaijmakers			
	A2	6,551,399	1/28/03	Mc Collum Etchason, et al.			
	A3	6,540,838	4/1/03	Sneh, et al.			
	A4	6,503,330	1/7/03	Sneh, et al.			
	A5	6,551,339	4/22/03	Gavrinsky			
	A6						
	A7						

#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	B1	WO02/27063	4/4/02	PCT			X	

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	"Atomic Layer Deposition of Metal Oxide Thin Films," A thesis presented by Dennis Michael Hausmann, Harvard University, 186 pages, July 2002.
	C2	Hausmann et al., "Rapid Vapor Deposition of Highly Conformal Silica Nanolaminates," Science, Vol. 308, October 2002, 5 Pages
	C3	
	C4	
	C5	
	C6	
Examiner		Date Considered

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.